

Silicon PNP Power Transistors

2SB1556

DESCRIPTION

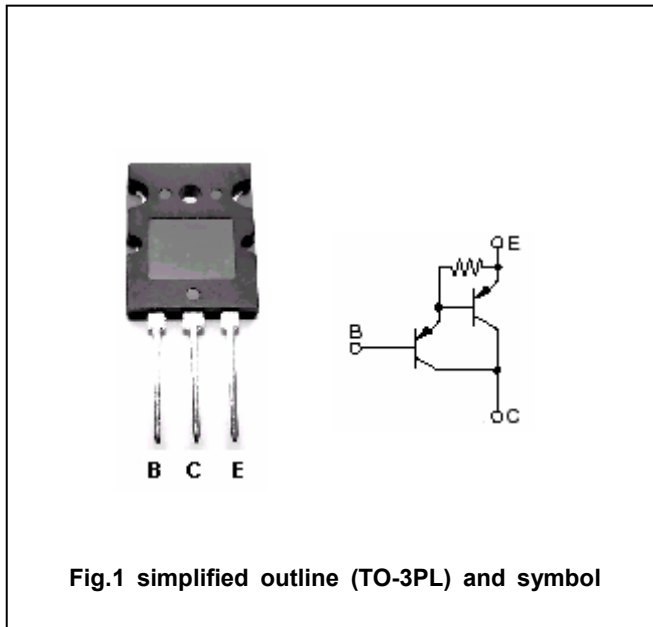
- With TO-3PL package
- Complement to type 2SD2385
- High DC current gain
- Low collector saturation voltage
- DARLINGTON

APPLICATIONS

- For power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-140	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-140	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current		-8	A
I <sub>B</sub>	Base current		-0.1	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	120	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-50mA ; I <sub>B</sub> =0	-140			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-7A ; I <sub>B</sub> =-7mA			-2.5	V
V <sub>BE</sub>	Base-emitter voltage	I <sub>C</sub> =-7A ; V <sub>CE</sub> =-5V			-3.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-140V ; I <sub>E</sub> =0			-5.0	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V ; I <sub>C</sub> =0			-5.0	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-7A ; V <sub>CE</sub> =-5V	5000		30000	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-12A ; V <sub>CE</sub> =-5V	2000			
C <sub>OB</sub>	Collector output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =-10V f=1MHz		170		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-5V		30		MHz

◆ h<sub>FE-2</sub> classifications

A	B	C
5000-12000	9000-18000	15000-30000

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PACKAGE OUTLINE

